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# FDMS86300

## N-Channel PowerTrench<sup>®</sup> MOSFET

80 V, 122 A, 3.9 mΩ

### Features

- Max  $r_{DS(on)}$  = 3.9 mΩ at  $V_{GS} = 10\text{ V}$ ,  $I_D = 19\text{ A}$
- Max  $r_{DS(on)}$  = 5.5 mΩ at  $V_{GS} = 8\text{ V}$ ,  $I_D = 15.5\text{ A}$
- Advanced Package and Silicon combination for low  $r_{DS(on)}$  and high efficiency
- Next generation enhanced body diode technology, engineered for soft recovery
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

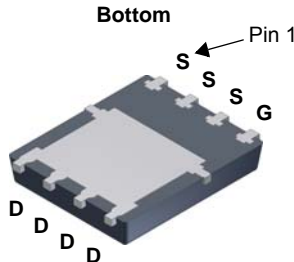


### General Description

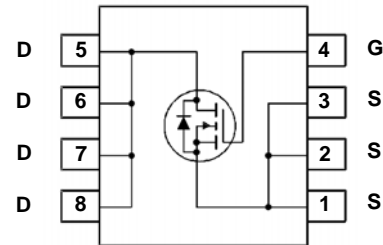
This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $r_{DS(on)}$ , fast switching speed and body diode reverse recovery performance.

### Applications

- OringFET / Load Switching
- DC-DC Conversion



Power 56



### MOSFET Maximum Ratings $T_A = 25\text{ °C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
$V_{DS}$	Drain to Source Voltage	80	V
$V_{GS}$	Gate to Source Voltage	±20	V
$I_D$	Drain Current -Continuous	$T_C = 25\text{ °C}$	122
	-Continuous	$T_C = 100\text{ °C}$	78
	-Continuous	$T_A = 25\text{ °C}$ (Note 1a)	19
	-Pulsed	(Note 4)	556
$E_{AS}$	Single Pulse Avalanche Energy	(Note 3)	252
$P_D$	Power Dissipation	$T_C = 25\text{ °C}$	104
	Power Dissipation	$T_A = 25\text{ °C}$ (Note 1a)	2.5
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS86300	FDMS86300	Power 56	13 "	12 mm	3000 units

## Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}, V_{GS} = 0\ \text{V}$	80			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$		39		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 64\ \text{V}, V_{GS} = 0\ \text{V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\ \text{V}, V_{DS} = 0\ \text{V}$			$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	2.5	3.4	4.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$		-11		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ \text{V}, I_D = 19\ \text{A}$		3.2	3.9	m $\Omega$
		$V_{GS} = 8\ \text{V}, I_D = 15.5\ \text{A}$		3.8	5.5	
		$V_{GS} = 10\ \text{V}, I_D = 19\ \text{A}, T_J = 125^\circ\text{C}$		5.0	5.8	
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\ \text{V}, I_D = 19\ \text{A}$		60		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 40\ \text{V}, V_{GS} = 0\ \text{V}, f = 1\ \text{MHz}$		5325	7082	pF
$C_{oss}$	Output Capacitance			957	1272	pF
$C_{rss}$	Reverse Transfer Capacitance			26	63	pF
$R_g$	Gate Resistance			1.2		$\Omega$

### Switching Characteristics

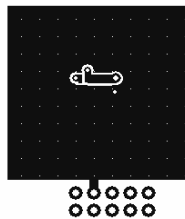
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 40\ \text{V}, I_D = 19\ \text{A}, V_{GS} = 10\ \text{V}, R_{GEN} = 6\ \Omega$		31	50	ns	
$t_r$	Rise Time			26	43	ns	
$t_{d(off)}$	Turn-Off Delay Time			36	58	ns	
$t_f$	Fall Time			9	18	ns	
$Q_g$	Total Gate Charge		$V_{GS} = 0\ \text{V to } 10\ \text{V}$		72	86	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\ \text{V to } 8\ \text{V}$	$V_{DD} = 40\ \text{V}, I_D = 19\ \text{A}$		59	71	nC
$Q_{gs}$	Gate to Source Charge			28.2		nC	
$Q_{gd}$	Gate to Drain "Miller" Charge			14.9		nC	

### Drain-Source Diode Characteristics

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\ \text{V}, I_S = 2.1\ \text{A}$ (Note 2)		0.71	1.2	V
		$V_{GS} = 0\ \text{V}, I_S = 19\ \text{A}$ (Note 2)		0.81	1.3	
$t_{rr}$	Reverse Recovery Time	$I_F = 19\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		57	90	ns
$Q_{rr}$	Reverse Recovery Charge			50	80	nC
$t_{rr}$	Reverse Recovery Time	$I_F = 19\ \text{A}, di/dt = 300\ \text{A}/\mu\text{s}$		48	77	ns
$Q_{rr}$	Reverse Recovery Charge			103	165	nC

#### Notes:

- $R_{\theta JA}$  is determined with the device mounted on a  $1\ \text{in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\ \text{in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $50^\circ\text{C}/\text{W}$  when mounted on a  $1\ \text{in}^2$  pad of 2 oz copper



b)  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper.

- Pulse Test: Pulse Width  $< 300\ \mu\text{s}$ , Duty cycle  $< 2.0\%$ .
- $E_{AS}$  of 252 mJ is based on starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.3\ \text{mH}$ ,  $I_{AS} = 41\ \text{A}$ ,  $V_{DD} = 72\ \text{V}$ ,  $V_{GS} = 10\ \text{V}$ .
- Pulse  $I_d$  limited by junction temperature,  $t_d \leq 100\ \mu\text{s}$ , please refer to SOA curve for more details.

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted

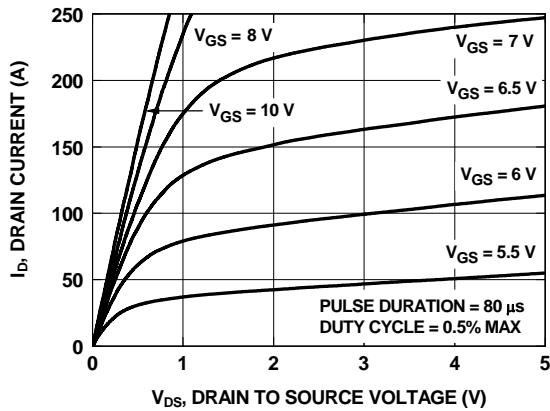


Figure 1. On-Region Characteristics

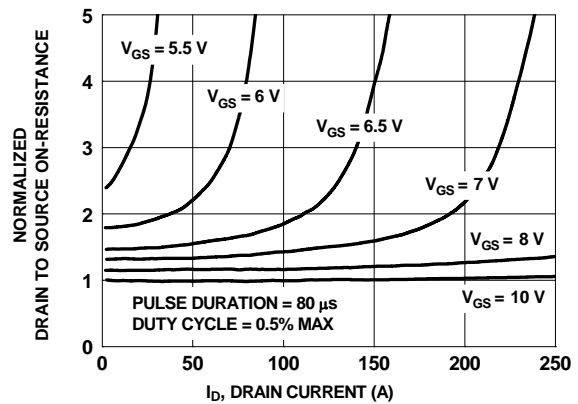


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

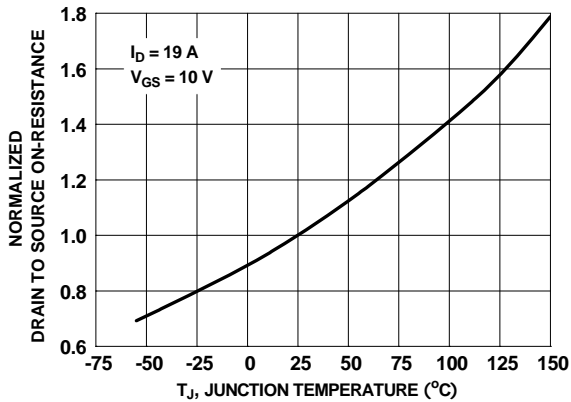


Figure 3. Normalized On-Resistance vs Junction Temperature

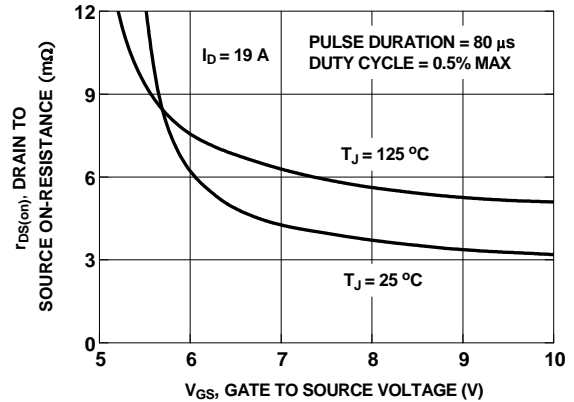


Figure 4. On-Resistance vs Gate to Source Voltage

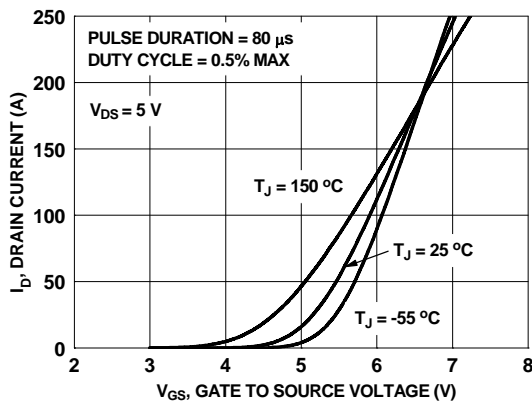


Figure 5. Transfer Characteristics

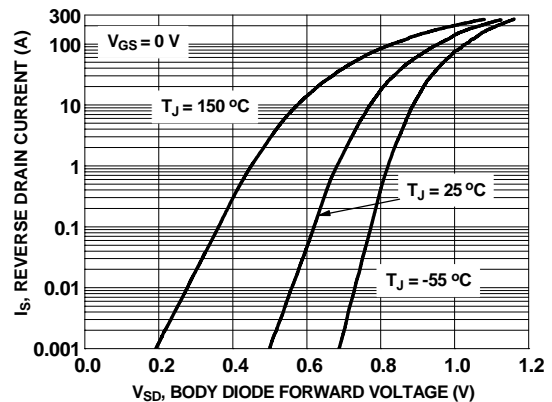
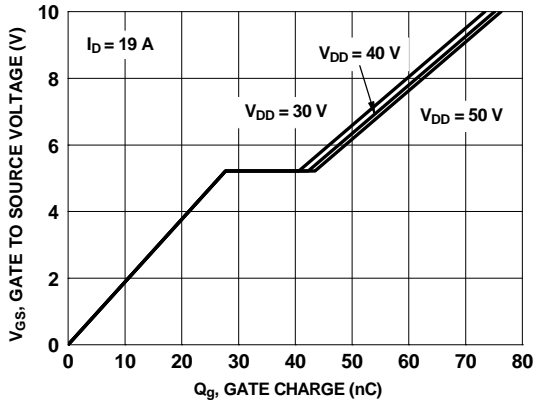
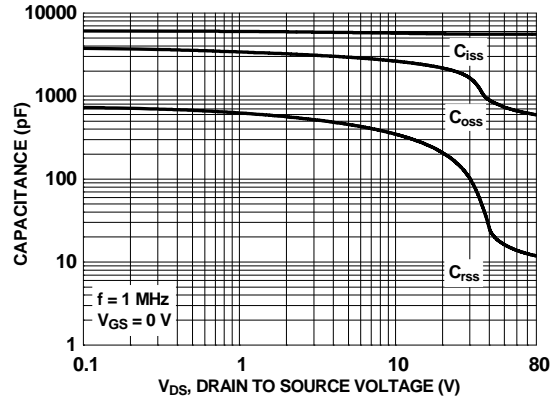


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

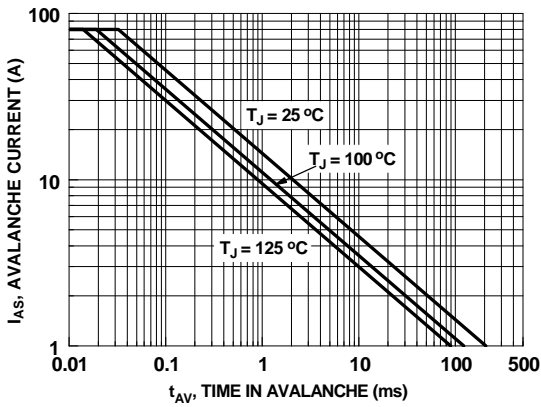
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



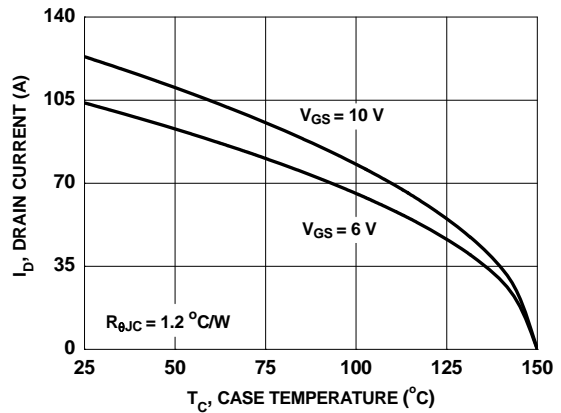
**Figure 7. Gate Charge Characteristics**



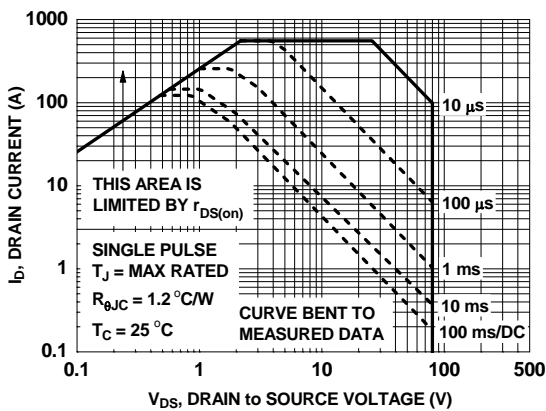
**Figure 8. Capacitance vs Drain to Source Voltage**



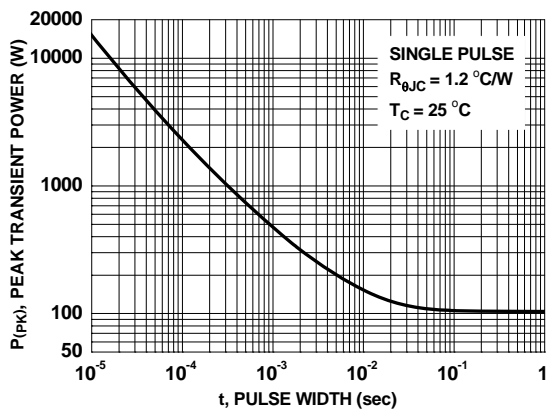
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs Case Temperature**

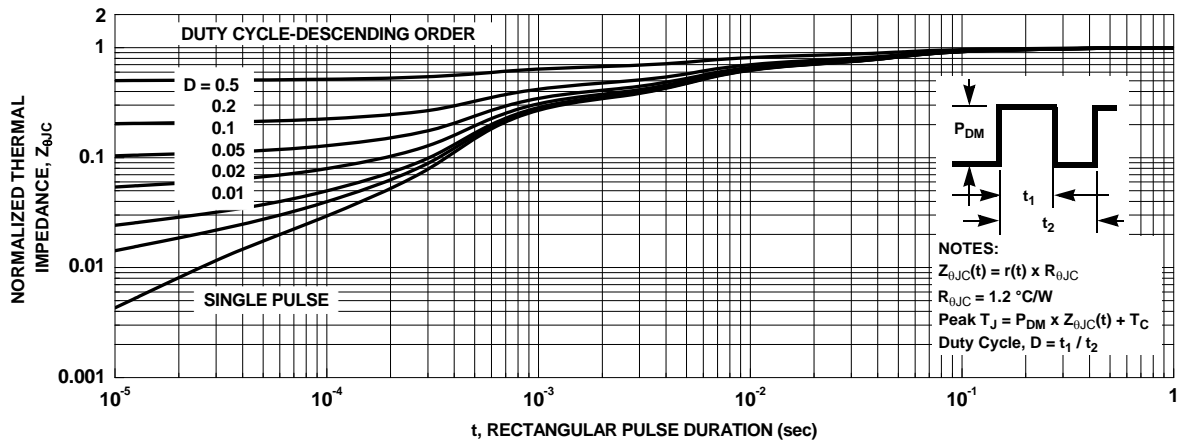


**Figure 11. Forward Bias Safe Operating Area**



**Figure 12. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



**Figure 13. Junction-to-Case Transient Thermal Response Curve**



TOP VIEW



LAND PATTERN RECOMMENDATION

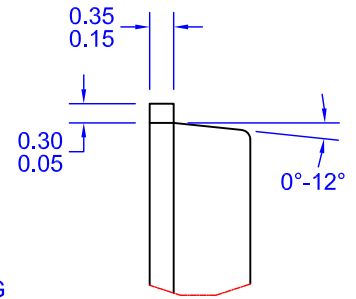


SIDE VIEW

OPTIONAL DRAFT ANGLE MAY APPEAR ON FOUR SIDES OF THE PACKAGE



DETAIL C  
SCALE: 2:1



DETAIL B  
SCALE: 2:1



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

- A. PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA, DATED OCTOBER 2002.
- B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- E. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.
- F. DRAWING FILE NAME: PQFN08AREV10



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